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ELECTRONIC SUPPLEMENTARY INFORMATION

Three-dimensionally-architectured GaN light emitting crystals

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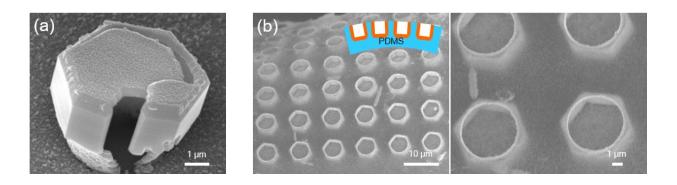


Figure S1. (a) SEM image of broken GaN crystal. (b) SEM images of GaN crystal array embedded in PDMS and mechanically exploited from the substrate.

Electron Image

Element	Line Type	Wt%	Atomic %
Ga	K series	79.19	62.94
N	K series	4.44	17.58
С	K series	2.74	12.65
Pt	L series	11.46	3.25
0	K series	0.85	2.93

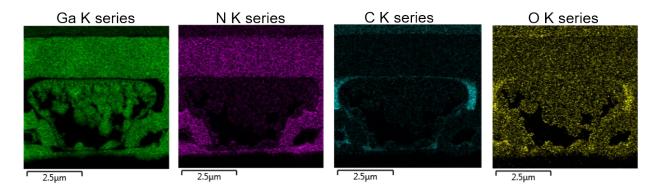


Figure S2. Top: TEM image (left panel) and corresponding EDS analysis result (right panel). Bottom: The corresponding elemental mapping images of Ga (green), N (purple), C (blue) and O (yellow).

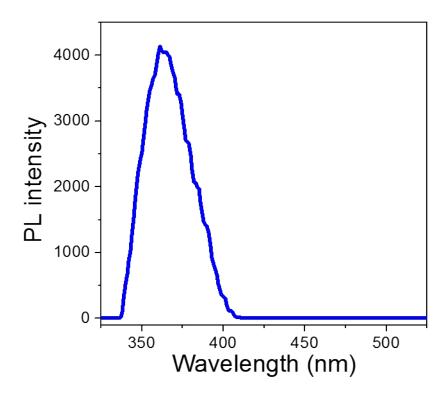


Figure S3. Room temperature PL spectrum of n-type GaN crystals.